

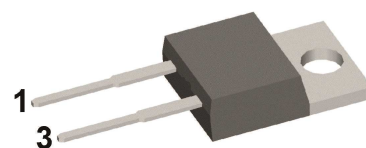
FRED

$$\begin{aligned} V_{RRM} &= 1000 \text{ V} \\ I_{FAV} &= 12 \text{ A} \\ t_{rr} &= 45 \text{ ns} \end{aligned}$$

Fast Recovery Epitaxial Diode Single Diode

Part number

DSEI12-10A



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

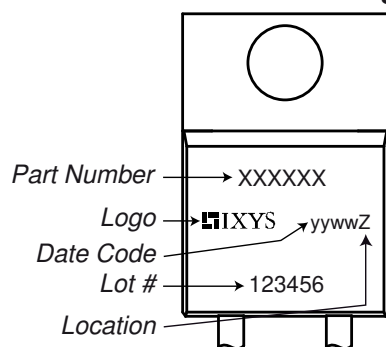
Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

Fast Diode				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				1000	V	
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				1000	V	
I _R	reverse current, drain current	V _R = 1000 V	T _{VJ} = 25°C			250	μA	
		V _R = 800 V	T _{VJ} = 125°C			4	mA	
V _F	forward voltage drop	I _F = 12 A	T _{VJ} = 25°C			2.68	V	
		I _F = 24 A				3.02	V	
		I _F = 12 A	T _{VJ} = 150°C			2.12	V	
		I _F = 24 A				2.57	V	
I _{FAV}	average forward current	T _C = 100°C rectangular d = 0.5	T _{VJ} = 150°C			12	A	
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 150°C		1.72	V	
r _F	slope resistance					34	mΩ	
R _{thJC}	thermal resistance junction to case					1.6	K/W	
R _{thCH}	thermal resistance case to heatsink				0.50		K/W	
P _{tot}	total power dissipation	T _C = 25°C				78	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		75	A	
C _J	junction capacitance	V _R = 500 V f = 1 MHz		T _{VJ} = 25°C	8		pF	
I _{RM}	max. reverse recovery current	} I _F = 12 A; V _R = 540 V -di _F /dt = 100 A/μs		T _{VJ} = 25 °C	4		A	
				T _{VJ} = 100 °C	7		A	
t _{rr}	reverse recovery time			T _{VJ} = 25 °C	90		ns	
				T _{VJ} = 100 °C	150		ns	

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			25	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI12-10A	DSEI12-10A	Tube	50	434434

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$

			Fast Diode	
$V_{0\max}$	threshold voltage	1.72		V
$R_{0\max}$	slope resistance *	31		mΩ

Outlines TO-220


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



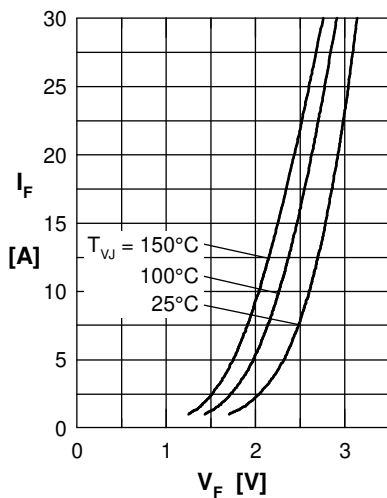
Fast Diode


Fig. 1 Forward current I_F versus max. forward voltage drop V_F

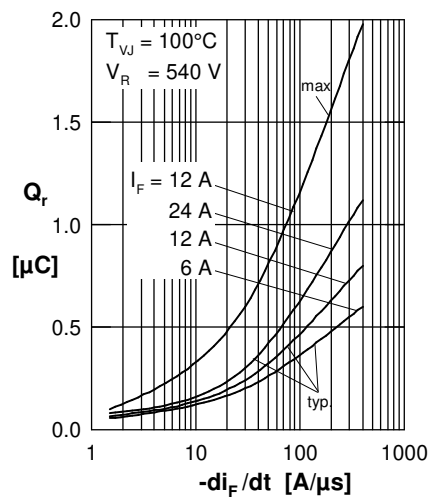


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

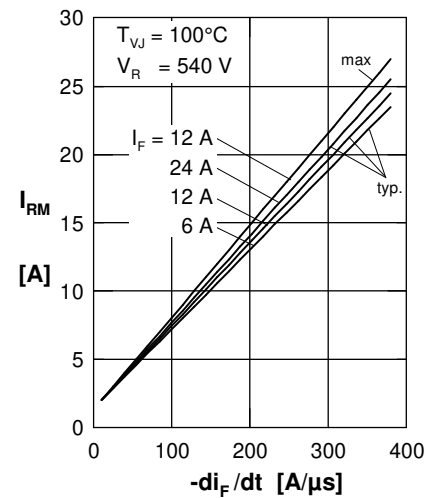


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

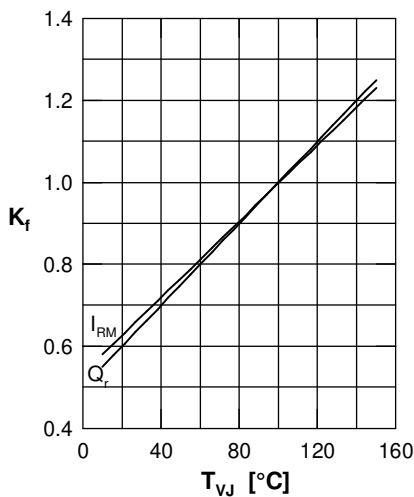


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

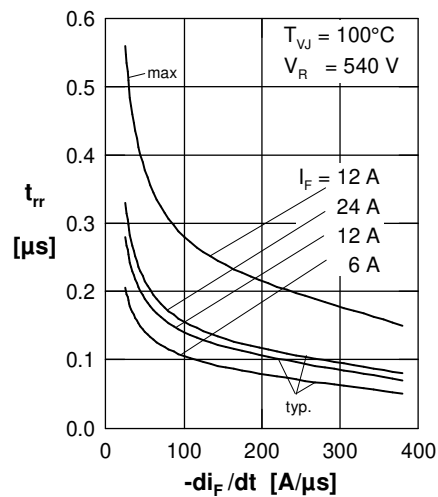


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

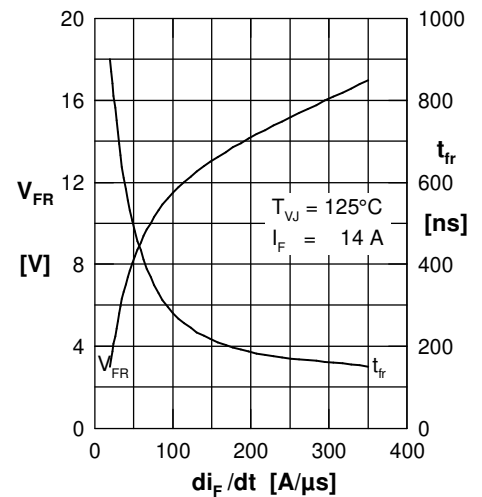


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

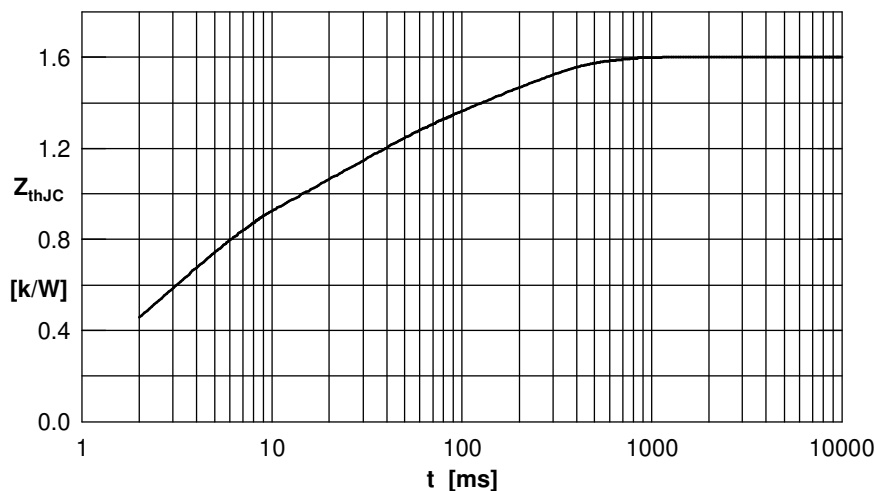


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.100	0.001
2	0.020	0.010
3	0.400	0.180
4	0.400	0.024
5	0.680	0.003